



IRF4104PBF Information

Part Number IRF4104PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 40V 75A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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IRF4104PBF Specifications

Manufacturer Part NumberIRF4104PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C75A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Urrent - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 20V #### 20V #### 20V #### 20V #### 20V #### 20V #### 25W ### 20V #### 25W ### 25W ### 25W ### 25V ### 2	Manufacturer Part Number	IRF4104PBF
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C75A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C75A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	HEXFET?
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C75A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 75A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 75A (Tc)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	75A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case 100nC @ 10V 140W 140W 140W 150 140W 150 140W 150 150 160 160 170 170 170 170 170 17	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	100nC @ 10V
FET Feature - 140W (Tc) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	3000pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs5.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	140W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	5.5 mOhm @ 75A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
-	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRF4104PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF4104PBF Payment Methods



















IRF4104PBF Shipping Methods













If you have any question about IRF4104PBF, please do not hesitate to contact us!

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